

COMPLEMENTARY SILICON POWER TRANSISTORS

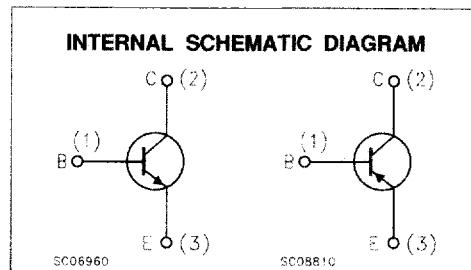
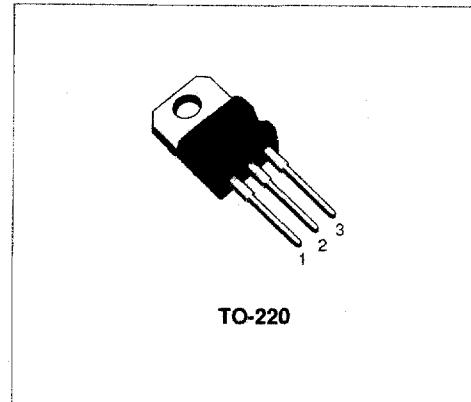
- SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The BD243B and BD243C are silicon epitaxial-base NPN transistors mounted in Jedec TO-220 plastic package.

They are intended for use in medium power linear and switching applications.

The complementary PNP types are BD244B and BD244C respectively.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value				Unit
		NPN	BD243B	BD243C		
		PNP	BD244B	BD244C		
V_{CB0}	Collector-Base Voltage ($I_E = 0$)		80	100		V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)		80	100		V
V_{EB0}	Emitter-Base Voltage ($I_C = 0$)			5		V
I_C	Collector Current			6		A
I_{CM}	Collector Peak Current			10		A
I_B	Base Current			2		A
P_{tot}	Total Dissipation at $T_c \leq 25^\circ C$			65		W
T_{stg}	Storage Temperature			-65 to 150		$^\circ C$
T_j	Max. Operating Junction Temperature			150		$^\circ C$

For PNP types voltage and current values are negative.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.92	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = \text{rated } V_{CEO}$			0.4	mA
I _{CEO}	Collector Cut-off Current ($I_B = 0$)	for BD243B/BD244B $V_{CE} = 60\text{ V}$ for BD243C/BD244C $V_{CE} = 60\text{ V}$			0.7 0.7	mA mA
I _{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			1	mA
$V_{CEO(sus)}$ *	Collector-Emitter Sustaining Voltage	$I_C = 30\text{ mA}$ for BD243B/BD244B for BD243C/BD244C	80 100			V V
$V_{CE(sat)}$ *	Collector-Emitter Saturation Voltage	$I_C = 6\text{ A}$ $I_B = 1\text{ A}$			1.5	V
V_{BE} *	Base-Emitter Voltage	$I_C = 6\text{ A}$ $V_{CE} = 4\text{ V}$			2	V
h_{FE} *	DC Current Gain	$I_C = 0.3\text{ A}$ $V_{CE} = 4\text{ V}$ $I_C = 3\text{ A}$ $V_{CE} = 4\text{ V}$	30 15			
h_{ie}	Small Signal Current Gain	$I_C = 0.5\text{ A}$ $V_{CE} = 10\text{ V}$ $f = 1\text{MHz}$ $I_C = 0.5\text{ A}$ $V_{CE} = 10\text{ V}$ $f = 1\text{KHz}$	3 20			

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

For PNP types voltage and current values are negative.